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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0039				
I _D (A)	100				
Configuration	Single				
Package	TO-263				

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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N-Channel MOSFET	3

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ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V _{DS}	60	V		
Gate-source voltage		V_{GS}	± 20	V		
Continuous drain current	$T_C = 25 ^{\circ}C^{a}$	1	100			
Continuous drain current	T _C = 125 °C	I _D	80			
Continuous source current (diode conduction	I _S	100	Α			
Pulsed drain current ^b	I _{DM}	320				
Single pulse avalanche current	L = 0.1 mH	I _{AS}	50			
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	125	mJ		
Maximum power dissipation ^b	T _C = 25 °C	P _D	150	W		
iviaximum power dissipation -	T _C = 125 °C	r D	50	VV		
Operating junction and storage temperature r	ange	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	LIMIT	UNIT			
Junction-to-ambient F	PCB mount c	R_{thJA}	40	°C/W			
Junction-to-case (drain)		R_{thJC}	1	G/W			

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V		1			
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	300	μΑ	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0032	0.0039	Ω	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0062		
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0075	1	
Forward transconductance b	9 _{fs}	V_{DS}	= 15 V, I _D = 20 A	-	135	-	S	
Dynamic ^b							•	
Input capacitance	C _{iss}			-	4841	6600		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	2243	3100	рF	
Reverse transfer capacitance	C _{rss}				60	85	1	
Total gate charge ^c	Qg			-	58	90		
Gate-source charge c	Q _{gs}	$V_{GS} = 10 \text{ V}$ $V_{DS} = 30 \text{ V}, I_D = 50 \text{ A}$		-	24	-	nC	
Gate-drain charge ^c	Q _{gd}			-	5	-		
Gate resistance	Rg	f = 1 MHz		0.6	1.26	1.9	Ω	
Turn-on delay time ^c	t _{d(on)}			-	19	30		
Rise time ^c	t _r	$V_{DD} = 30 \text{ V}, R_L = 0.6 \Omega$ $I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	10	20		
Turn-off delay time ^c	t _{d(off)}			-	30	50	ns -	
Fall time ^c	t _f			-	8	15		
Source-Drain Diode Ratings and Chara	cteristics ^b							
Pulsed current ^a	I _{SM}			-	-	320	Α	
Forward voltage	V_{SD}	I _F = 25 A, V _{GS} = 0 V		-	0.83	1.5	V	
Body diode reverse recovery time	t _{rr}	I _F = 30 A, di/dt = 100 A/μs		-	50	100	ns	
Body diode reverse recovery charge	Q_{rr}			-	55	110	nC	
Reverse recovery fall time	ta			-	24	-	İ	
Reverse recovery rise time	t _b			-	26	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.92	-	Α	

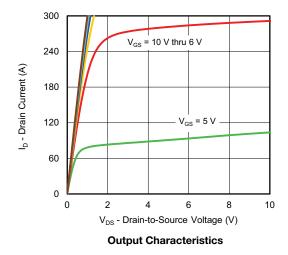
Notes

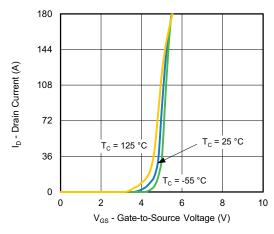
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

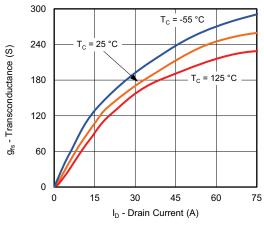


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

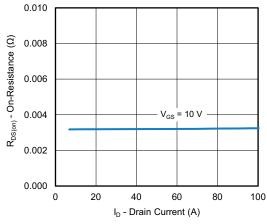




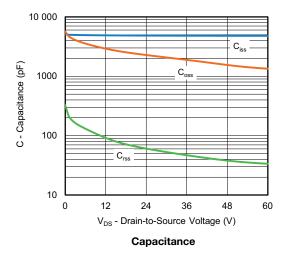
Transfer Characteristics

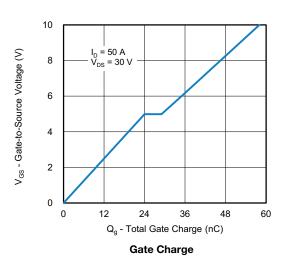


Transconductance



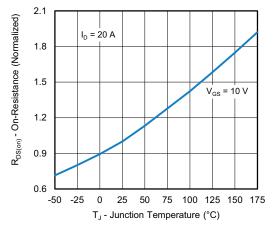
On-Resistance vs. Drain Current



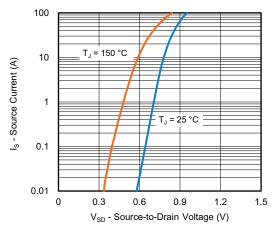




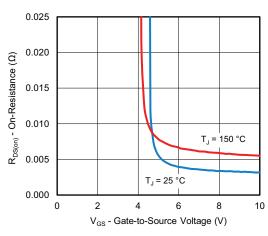
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



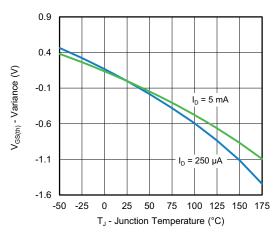
On-Resistance vs. Junction Temperature



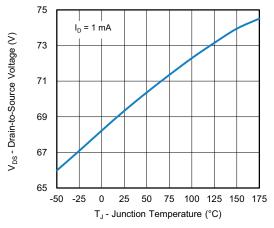
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



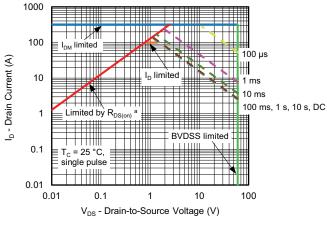
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



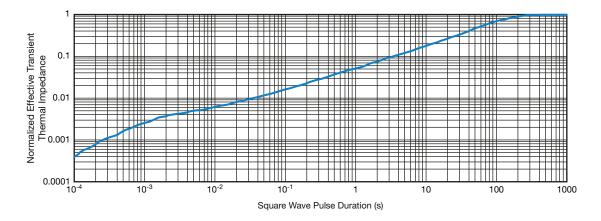
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

Note

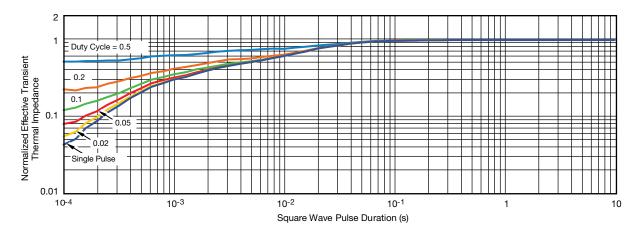
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

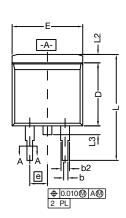
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

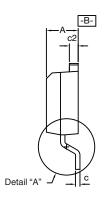
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

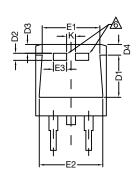
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76971.



TO-263 (D²PAK): 3-LEAD

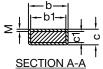








DETAIL A (ROTATED 90°)



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2:	П			<u>T</u>	5	ပ
,	SE	СТ	ION	ΙΔ-	Ι.Δ	t

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

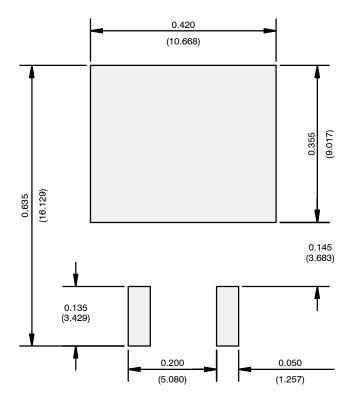
		INCHES		MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223 -		
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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